



GaN-Based Power Electronic Devices and Their Applications, 2nd Edition

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Message from the Guest Editors

Dear Colleagues,

Due to their excellent physical properties, gallium nitride (GaN) electric devices that can operate at a high switching frequency can drastically improve the energy conversion efficiency, reduce the volume of energy storage components, and scale down the system form factor. GaN has become one of the most promising materials in the area of high-power and high-temperature power electronics, and it is considered the material that will revolutionize the future of power electronics.

Impressive progress has already been achieved in lateral and vertical GaN device technologies, from advanced epitaxial growth approaches to novel or cost-effective device structures as well as innovative processing methods, more in-depth device physical analysis, and monolithic integration of GaN-based power electronic devices.

The main aim of this Special Issue is to bring the latest and most important innovations in GaN-based power electronic devices and their applications, address recent breakthroughs in GaN power electronics, and provide an up-to-date picture of current challenges and future development.





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Message from the Editor-in-Chief

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